UNR51A1G

Silicon PNP epitaxial planar type

For digital circuits

■ Features

- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- SMini type package allowing easy automatic insertion through tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-50	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Collector current	I_{C}	-80	mA	
Total power dissipation	P_{T}	150	mW	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

■ Package

- Code
 - SMini3-F2
- Pin Name
 - 1: Base
 - 2: Emitter
 - 3: Collector
- Marking Symbol: CE
- Internal Connection

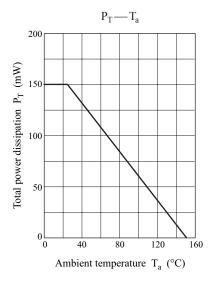
$$\begin{array}{c|c} R_1 & (10 \text{ k}\Omega) \\ B & & & \\ R_2 & & \\ (10 \text{ k}\Omega) & & & \\ \end{array} \qquad \begin{array}{c} C \\ \\ \end{array}$$

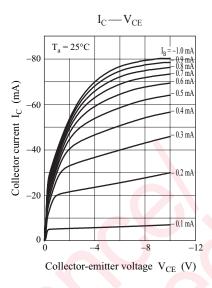
■ Electrical Characteristics $T_a = 25$ °C±3°C

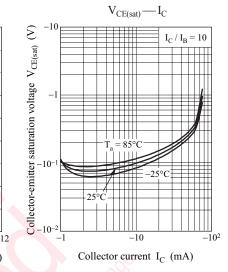
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$	60.		- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -50 \text{ V}, I_{B} = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			- 0.5	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	35			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V_{OH}	$V_{CC} = -5 \text{ V}, V_{B} = -0.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V _{OL}	$V_{CC} = -5 \text{ V}, V_{B} = -2.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$			-0.2	V
Input resistance	R_1		-30%	10	+30%	$k\Omega$
Resistance ratio	R_1/R_2		0.8	1	1.2	_
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

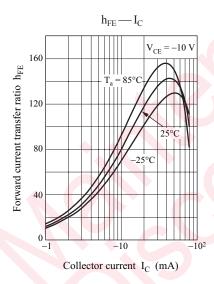
 $Note) \quad \text{Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS~C~7030~measuring~methods~for~transistors.}$

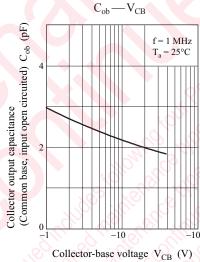
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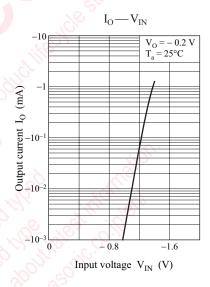


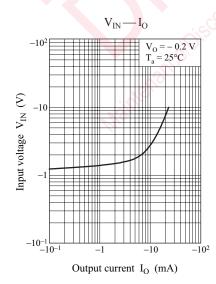








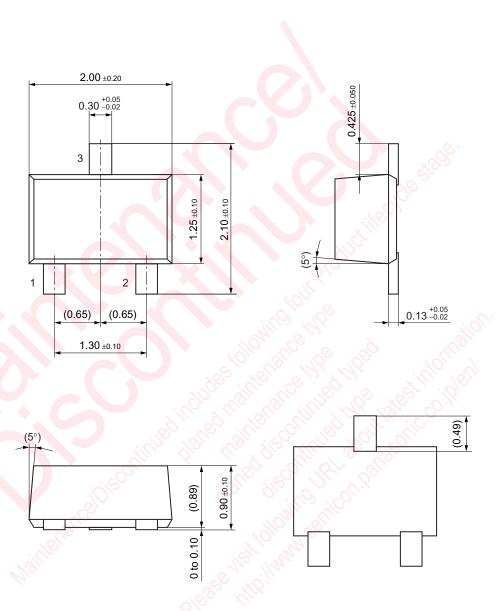




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Panasonic UNR51A1G

SMini3-F2 Unit: mm



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